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TITLE OF THE INVENTION
METHOD OF FAULT DETECTION FOR
MATERIAL PROCESS SYSTEM

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application claims priority and is related to United States application serial no. 60/343,175, filed on December 31, 2001, the contents of which are herein incorporated by

reference. This application is related to co-pending PCT application serial no.

PCT/US02/38990, filed on even date herewith, Attorney Docket No. 216951WO, the contents of which are herein incorporated by reference.

Change(s)
applied
to document,
/J.M.R./
4/20/2011

BACKGROUND OF THE INVENTION

Field of the Invention

[0002] The present invention relates to material processing and more particularly to a method for fault detection for material process system.

Description of Related Art

[0003] One area of material processing in the semiconductor industry which presents formidable challenges is, for example, the manufacture of integrated circuits (ICs). Demands for increasing the speed of ICs in general, and memory devices in particular, force semiconductor manufacturers to make devices smaller and smaller on the wafer surface. And conversely, while shrinking device sizes on the substrate is incurred, the number of devices fabricated on a single substrate is dramatically increased with further expansion of the substrate diameter (or processing real estate) from 200 mm to 300 mm and greater. Both the reduction in feature size, which places greater emphasis on critical dimensions (CD), and the increase of substrate size lead to even greater requirements on material processing uniformity to maximize the yield of superior devices.